

# **CPH3246**-

# NPN Epitaxial Planar Silicon Transistor **High-Current Switching Applications**

# **Applications**

• DC / DC converters, relay drivers, lamp drivers, motor drivers, inverters.

### Features

- Adoption of FBET, MBIT processes.
- · Large current capacitance.
- · Low collector-to-emitter saturation voltage.
- · High-speed switching.
- Ultrasmall package permitting applied sets to be small and slim (mounting height: 0.9mm).
- · High allowable power dissipation.

# Specifications

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		100	V
Collector-to-Emitter Voltage	VCES		100	V
Collector-to-Emitter Voltage	VCEO		60	V
Emitter-to-Base Voltage	VEBO		6.5	V
Collector Current	IC		3	А
Collector Current (Pulse)	ICP		5	А
Base Current	IB		600	mA
Collector Dissipation	PC	Mounted on a ceramic board (600mm <sup>2</sup> X0.8mm)	0.9	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

#### Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions		Ratings		
	Symbol		min	typ	max	Unit
Collector Cutoff Current	ICBO	VCB=50V, IE=0A			1	μΑ
Emitter Cutoff Current	IEBO	VEB=4V, IC=0A			1	μΑ
DC Current Gain	hFE	V <sub>CE</sub> =2V, I <sub>C</sub> =100mA	300		600	
Gain-Bandwidth Product	fT	VCE=10V, IC=500mA		390		MHz
Output Capacitance	Cob	V <sub>CB</sub> =10V, f=1MHz		15		pF
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Marking : DR

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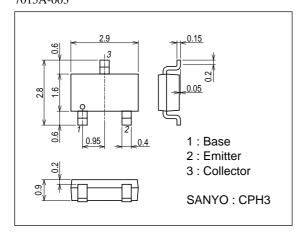
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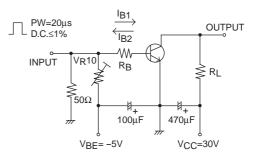
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Collector-to-Emitter Saturation Voltage	VCE(sat)1	IC=1A, IB=50mA		80	120	mV
	V <sub>CE</sub> (sat)2	I <sub>C</sub> =1A, I <sub>B</sub> =100mA		70	110	mV
Base-to-Emitter Saturation Voltage	VBE(sat)	IC=1A, IB=100mA		0.85	1.2	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	IC=10μΑ, IE=0Α	100			V
Collector-to-Emitter Breakdown Voltage	V(BR)CES	I <sub>C</sub> =100μA, R <sub>BE</sub> =0Ω	100			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	IC=1mA, RBE=∞	60			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I <sub>E</sub> =10μA, I <sub>C</sub> =0A	6.5			V
Turn-ON Time	ton	See specified Test Circuit.		35		ns
Storage Time	tstg	See specified Test Circuit.		680		ns
Fall Time	tf	See specified Test Circuit.		24		ns

#### **Package Dimensions**

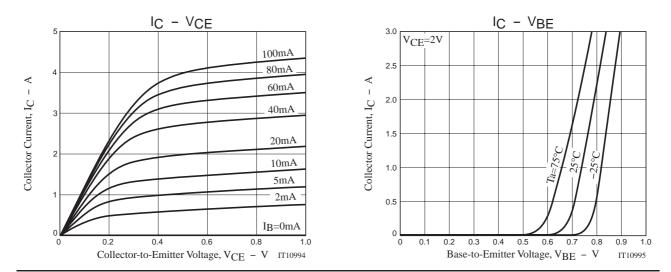
unit : mm 7015A-003

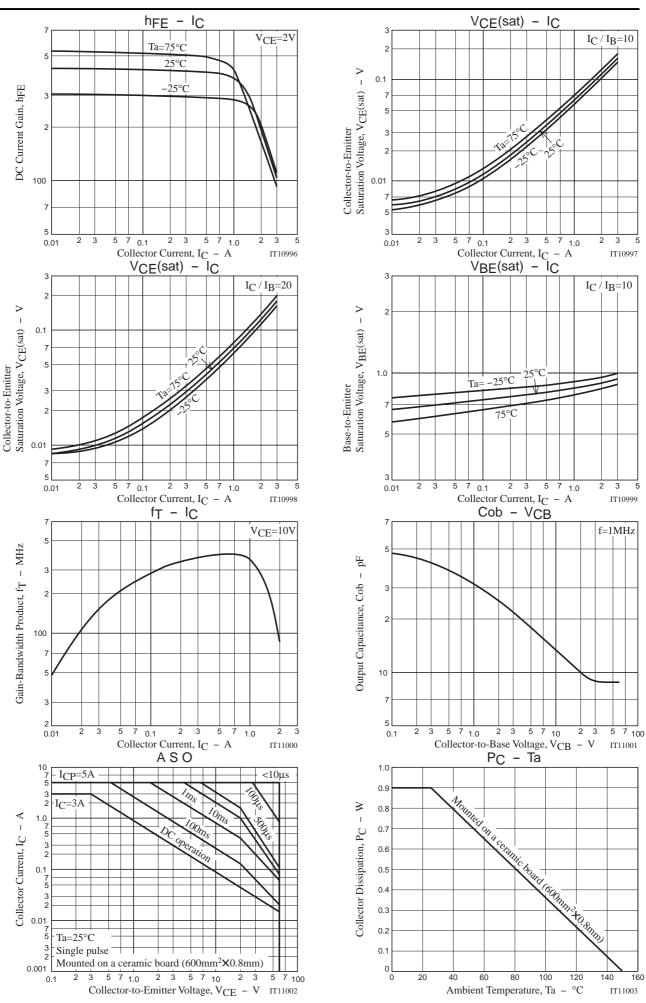


#### **Switching Time Test Circuit**



 $10I_{B1} = -10I_{B2} = I_C = 0.5A$ 





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